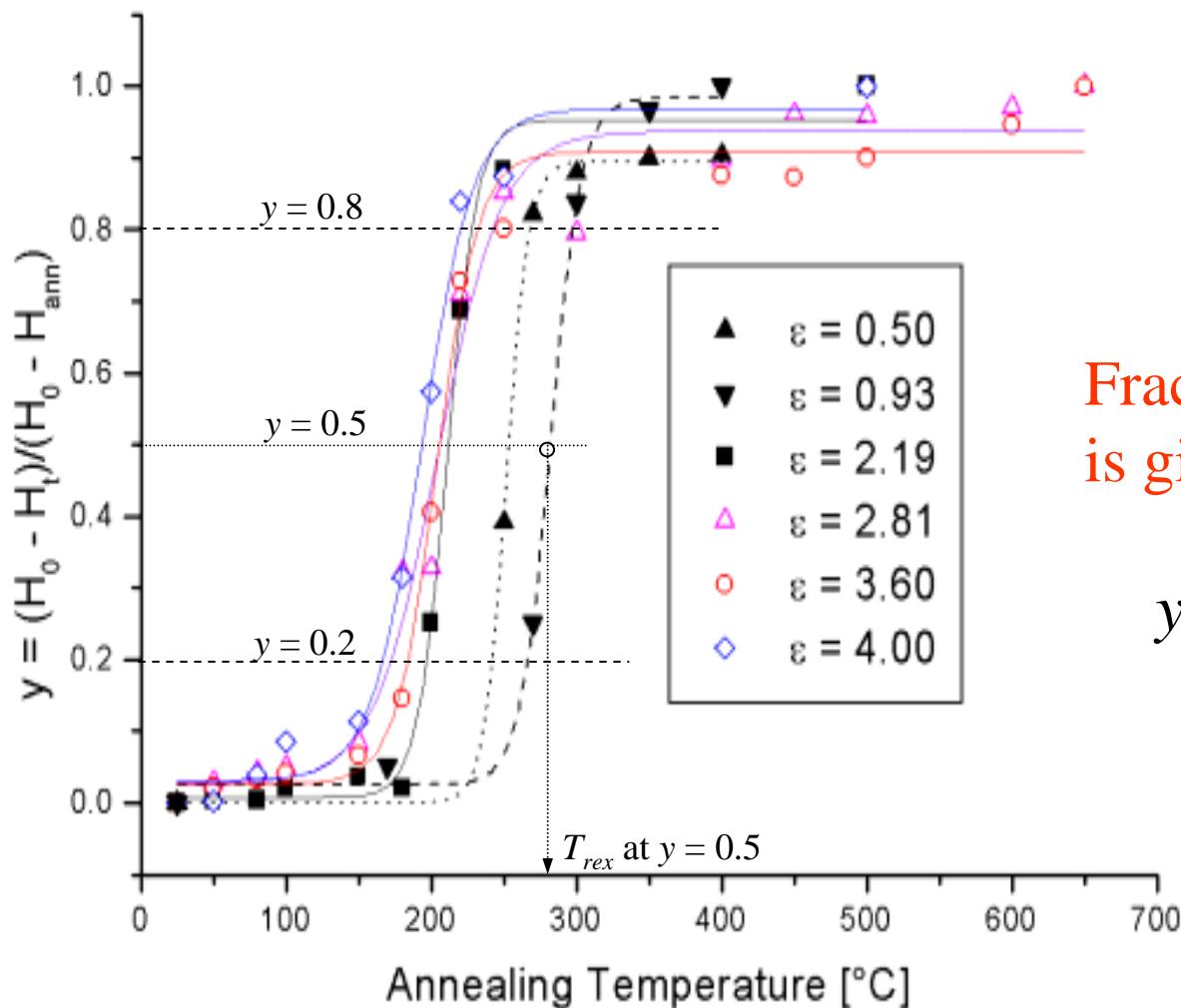


RECRYSTALLIZATION TEMPERATURE



Fraction transformed
is given by

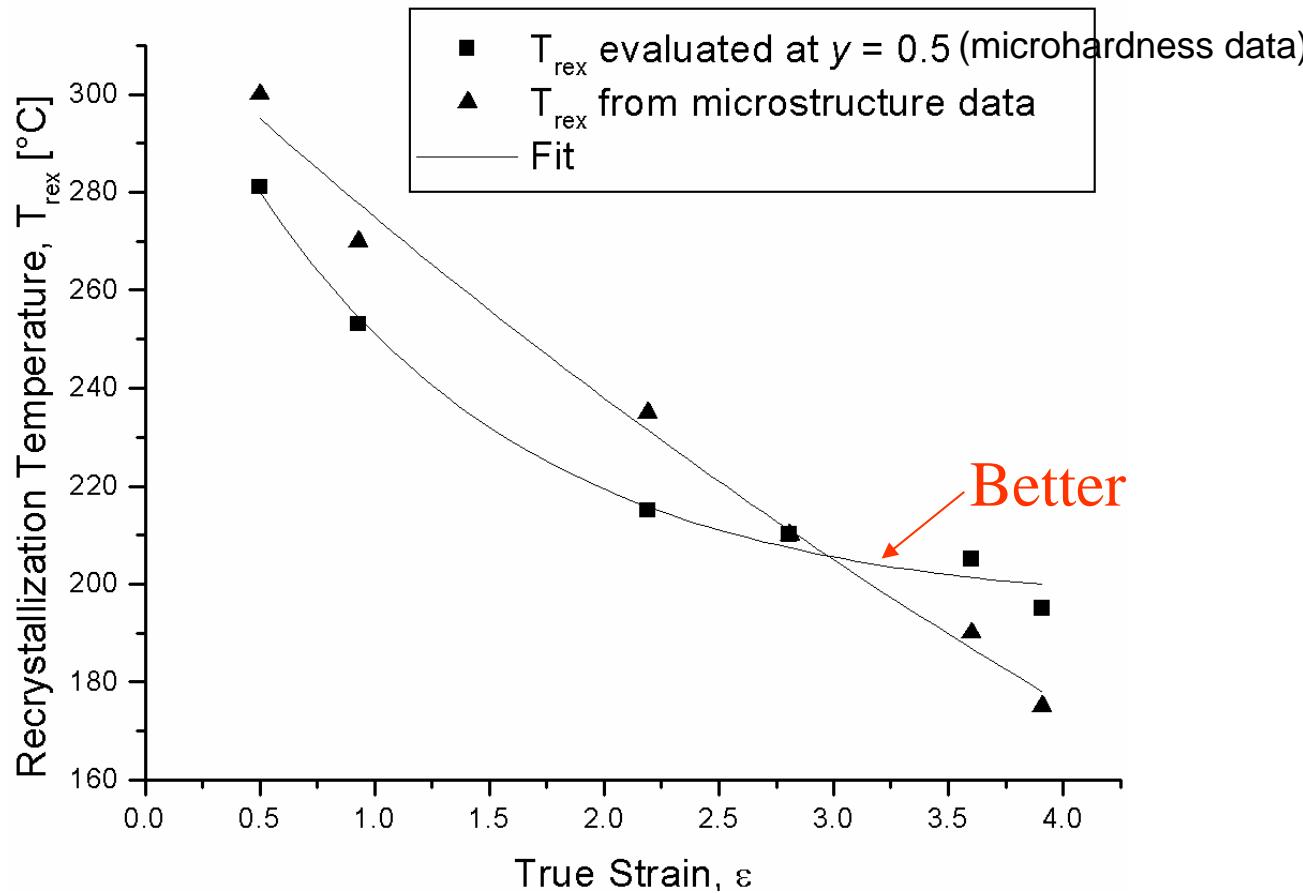
$$y = \frac{(H_0 - H_t)}{(H_0 - H_{ann})}$$

RESULTS – RECRYSTALLIZATION TEMPERATURE

T_{rex} , defined as the temperature at which the material is 50% recrystallized when annealing is carried out for 1 hour

- Methods used to determine T_{rex}
 - microstructural observation using optical microscope
 - evaluated from microhardness (i.e. at $y = 0.5$).

RESULTS – RECRYSTALLIZATION TEMPERATURE



Effect of processing strain on the recrystallization temperature of heavily drawn OFHC copper wires

RESULTS – PROPOSED MODEL

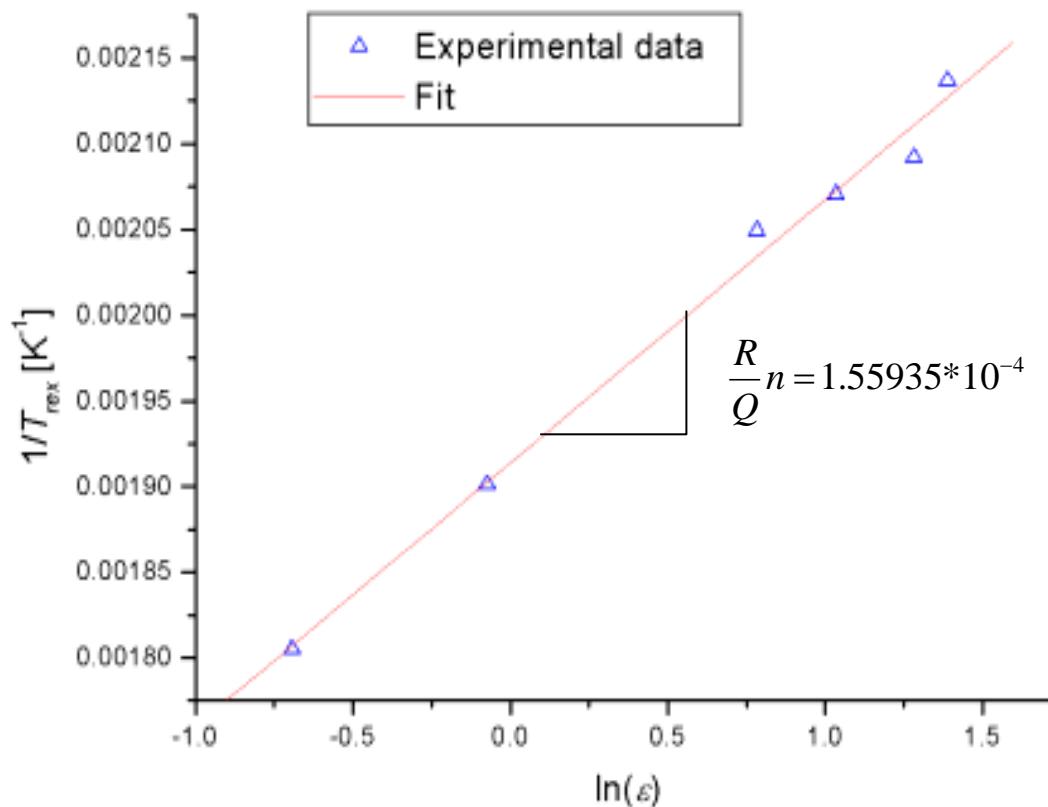
- Time for 50% static recrystallization ($t_{0.5}$) is temperature dependent and is often found to obey an Arrhenius type relationship of the form

$$t_{0.5}^{-1} = c \exp\left(-\frac{Q}{RT}\right)$$

- From experimental data, $t_{0.5} \propto \varepsilon^n$
- Thus, $\varepsilon^{-n} = A \exp\left(-\frac{Q}{RT_{rex}}\right)$
- Which can be rearranged to

$$\frac{1}{T_{rex}} = \frac{R}{Q} n \ln \varepsilon + \frac{R}{Q} \ln A$$

RECRYSTALLIZATION TEMPERATURE



- With $n = 4$, and $R = 8.314472 \text{ Jmol}^{-1}\text{K}^{-1}$, the activation energy, $Q \approx 200 \text{ kJmol}^{-1}$ (very close to the activation energy for lattice diffusion, $Q_v = 197 \text{ kJ/mol}$)